

L Number	Hits	Search Text	DB	Time stamp
5	19	polysilicon adj reoxidation	USPAT; EPO; JPO; IBM_TDB	2003/03/31 11:13
6	2	halo adj (implantation or implanting)	USPAT; EPO; JPO; IBM_TDB	2003/03/31 11:05
7	1023	gate and electrodes and (spacer or "offset spacer") and polysilicon and "etch stop"	USPAT; EPO; JPO; IBM_TDB	2003/03/31 11:07
8	15	(gate and electrodes and (spacer or "offset spacer") and polysilicon and "etch stop") and (reoxidation or reoxidating) and (implating or implantation) and source and drain	USPAT; EPO; JPO; IBM_TDB	2003/03/31 11:03
9	58	halo adj (implantation or implanting) or "halo implantation"	USPAT; EPO; JPO; IBM_TDB	2003/03/31 11:06
10	3	(gate and electrodes and (spacer or "offset spacer") and polysilicon and "etch stop") and (halo adj (implantation or implanting) or "halo implantation")	USPAT; EPO; JPO; IBM_TDB	2003/03/31 11:06
11	803	gate and electrodes and ("silicon oxide" or SiO or dielectric or insulating) and ("silicon nitride" or SiN) and (spacer or "offset spacer") and polysilicon and "etch stop"	USPAT; EPO; JPO; IBM_TDB	2003/03/31 11:11
12	203	(gate and electrodes and ("silicon oxide" or SiO or dielectric or insulating) and ("silicon nitride" or SiN) and (spacer or "offset spacer") and polysilicon and "etch stop") and (CHF3 or "CHF.sub.3")	USPAT; EPO; JPO; IBM_TDB	2003/03/31 11:12
13	122	(offset adj spacer) or "offset spacer"	USPAT; EPO; JPO; IBM_TDB	2003/03/31 11:13
14	19	(polysilicon adj reoxidation) and "polysilicon reoxidation"	USPAT; EPO; JPO; IBM_TDB	2003/03/31 11:15
15	1	5783475.pn.	USPAT; EPO; JPO; IBM_TDB	2003/03/31 11:19
16	3108	((438/283) or (438/290) or (438/291) or (438/300) or (438/301) or (438/706) or (438/710)).CCLS.	USPAT; EPO; JPO; IBM_TDB	2003/03/31 11:20
17	83	((438/283) or (438/290) or (438/291) or (438/300) or (438/301) or (438/706) or (438/710)).CCLS.) and (gate and electrodes and (spacer or "offset spacer") and polysilicon and "etch stop")	USPAT; EPO; JPO; IBM_TDB	2003/03/31 11:20
18	1640	((438/283) or (438/290) or (438/291) or (438/300) or (438/301)).CCLS.	USPAT; EPO; JPO; IBM_TDB	2003/03/31 11:21
20	61	((438/283) or (438/290) or (438/291) or (438/300) or (438/301)).CCLS.) and (gate and electrodes and (spacer or "offset spacer") and polysilicon and "etch stop")	USPAT; EPO; JPO; IBM_TDB	2003/03/31 11:21